

Samuel Shutts

List of Publications by Year in descending order

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16
papers

757
citations

1307594

7
h-index

1372567

10
g-index

17
all docs

17
docs citations

17
times ranked

1147
citing authors

#	ARTICLE	IF	CITATIONS
1	Electrically pumped continuous-wave III-V quantum dot lasers on silicon. <i>Nature Photonics</i> , 2016, 10, 307-311.	31.4	665
2	In situ annealing enhancement of the optical properties and laser device performance of InAs quantum dots grown on Si substrates. <i>Optics Express</i> , 2016, 24, 6196.	3.4	26
3	Temperature-Dependent Threshold Current in InP Quantum-Dot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2011, 17, 1343-1348.	2.9	15
4	Exploring the wavelength range of InP/AlGaInP QDs and application to dual-state lasing. <i>Semiconductor Science and Technology</i> , 2015, 30, 044002.	2.0	10
5	Degradation of III-V Quantum Dot Lasers Grown Directly on Silicon Substrates. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019, 25, 1-6.	2.9	10
6	Absorption, Gain, and Threshold in InP/AlGaInP Quantum Dot Laser Diodes. <i>IEEE Journal of Quantum Electronics</i> , 2013, 49, 389-394.	1.9	7
7	Monolithic InP Quantum Dot Mode-Locked Lasers Emitting at 730 nm. <i>IEEE Photonics Technology Letters</i> , 2020, 32, 1073-1076.	2.5	7
8	VCSEL Quick Fabrication for Assessment of Large Diameter Epitaxial Wafers. <i>IEEE Photonics Journal</i> , 2022, 14, 1-10.	2.0	6
9	Optical gain and absorption of 1.55- μm InAs quantum dash lasers on silicon substrate. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	5
10	Sub-mA Threshold Current Vertical Cavity Surface Emitting Lasers with a Simple Fabrication Process. , 2021, , .		2
11	Degradation Studies of InAs / GaAs QD Lasers Grown on Si. , 2018, , .		1
12	Temperature Dependent Behavior of the Optical Gain and Electroabsorption Modulation Properties of an InAs/GaAs Quantum Dot Epistucture. , 2019, , .		1
13	150mm full wafer fabrication and characterization of 940nm emitting VCSELs for high-volume manufacture. , 2021, , .		1
14	Quick Fabrication VCSELs for Characterisation of Epitaxial Material. <i>Applied Sciences (Switzerland)</i> , 2021, 11, 9369.	2.5	1
15	Increasing Maximum Gain in InAs Quantum Dot Lasers on GaAs and Si. , 2018, , .		0
16	The limits to peak modal gain in p-modulation doped indium arsenide quantum dot laser diodes. , 2021, , .		0